SCLS336H - MARCH 1996 - REVISED JANUARY 2000

2LE

25

24

 EPIC™ (Enhanced-Performance Implanted CMOS) Process Inputs Are TTL-Voltage Compatible 10E [1 48] 1LE 101 	GE PACKAGE
Distributed V _{CC} and GND Pins Minimize 1Q2 [3 46] 1D2 High-Speed Switching Noise GND [4 45] GND	
 Flow-Through Architecture Optimizes PCB Layout 1Q3 5 44 1D3 1Q4 6 43 1D4 	
 Latch-Up Performance Exceeds 250 mA Per JESD 17 V_{CC} 7 42 V_{CC} 1Q5 8 41 1D5 1Q6 9 40 1D6 	
• ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pE B = 0)	
Package Options Include Plastic Shrink 2Q1 [13 36] 2D1 Small-Outline (DL), Thin Shrink 2Q2 [14 35] 2D2	
Small-Outline (DGV) Packages and 380-mil 2Q3 16 33 2D3 Fine-Pitch Ceramic Flat (WD) Package 2Q4 17 32 2D4	
Using 25-mil Center-to-Center Spacings $V_{CC} \begin{bmatrix} 1 \\ 18 \end{bmatrix}_{18} = 31 \begin{bmatrix} V_{CC} \end{bmatrix}_{18}$	
description 2Q5 [19 30] 2D5	
Clear2Q620292D6The 'AHCT16373 devices are 16-bit transparentGND2128GNDD-type latches with 3-state outputs designed2Q722272D7specifically for driving highly capacitive or2Q823262D8	

D-type latches with 3-state outputs designed specifically for driving highly capacitive or relatively low-impedance loads. They are particularly suitable for implementing buffer registers, I/O ports, bidirectional bus drivers, and working registers.

These devices can be used as two 8-bit latches or one 16-bit latch. When the latch-enable (LE) input is high, the Q outputs follow the data (D) inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs.

A buffered output-enable (\overline{OE}) input can be used to place the eight outputs in either a normal logic state (high or low logic levels) or the high-impedance state. In the high-impedance state, the outputs neither load nor drive the bus lines significantly. The high-impedance state and the increased drive provide the capability to drive bus lines without need for interface or pullup components.

OE does not affect internal operations of the latch. Old data can be retained or new data can be entered while the outputs are in the high-impedance state.

To ensure the high-impedance state during power up or power down, \overline{OE} should be tied to V_{CC} through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

The SN54AHCT16373 is characterized for operation over the full military temperature range of -55° C to 125° C. The SN74AHCT16373 is characterized for operation from -40° C to 85° C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

EPIC and Widebus are trademarks of Texas Instruments Incorporated.

UNLESS OTHERWISE NOTED this document contains PRODUCTION DATA information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



Copyright © 2000, Texas Instruments Incorporated

SCLS336H - MARCH 1996 - REVISED JANUARY 2000

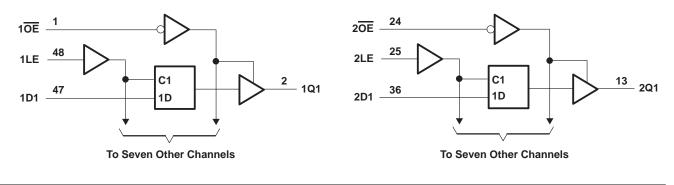
FUNCTION TABLE (each 8-bit latch)										
	INPUTS	OUTPUT								
OE	LE	D	Q							
L	Н	Н	Н							
L	Н	L	L							
L	L	Х	Q ₀							
Н	Х	Х	Z							

logic symbol[†]

1 <mark>0E</mark>	1	1EN		
1LE	48	C3		
20E	24	2EN		
2LE	25	C4		
222				
1D1	47	3D 1 ⊽	2	1Q1
1D2	46	30 1 1	3	1Q2
1D3	44		5	1Q3
1D4	43		6	1Q4
1D5	41		8	1Q5
1D6	40		9	1Q6
1D7	38		11	1Q7
1D8	37		12	1Q8
2D1	36	4D 2 ▽	13	2Q1
2D2	35		14	2Q2
2D3	33		16	2Q3
2D4	32		17	2Q4
2D5	30		19	2Q5
2D6	29		20	2Q6
2D7	27		22	2Q7
2D8	26		23	2Q8
			l	

 † This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





SCLS336H - MARCH 1996 - REVISED JANUARY 2000

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

	V nA nA nA MA VW VW
Storage temperature range, T _{stg} 65°C to 150°	°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 3)

		SN54AHC	T16373	SN74AHC	UNIT	
		MIN	MAX	MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	4.5	5.5	V
VIH	High-level input voltage	2	N	2		V
VIL	Low-level input voltage		0.8		0.8	V
VI	Input voltage	0	5.5	0	5.5	V
Vo	Output voltage	0	< Vcc	0	VCC	V
ЮН	High-level output current	20	-8		-8	mA
IOL	Low-level output current	20%	8		8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	9	20		20	ns/V
ТА	Operating free-air temperature	-55	125	-40	85	°C

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



SCLS336H - MARCH 1996 - REVISED JANUARY 2000

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	Vaa	T _A = 25°C			SN54AHC	T16373	SN74AHC	UNIT	
PARAMETER	TEST CONDITIONS	Vcc	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT
Varia	I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		4.4		V
VOH	I _{OH} = -8 mA	4.5 V	3.94			3.8		3.8		v
Ve	I _{OL} = 50 μA	4.5 V			0.1		0.1		0.1	V
VOL	I _{OL} = 8 mA	4.5 V			0.36		0.44		0.44	v
lj	$V_I = V_{CC}$ or GND	0 V to 5.5 V			±0.1	2	±1*		±1	μΑ
I _{OZ}	$V_{O} = V_{CC}$ or GND	5.5 V			±0.25		±2.5		±2.5	μΑ
ICC	$V_{I} = V_{CC} \text{ or GND}, \qquad I_{O} = 0$	5.5 V			4	200	40		40	μΑ
∆lCC [†]	One input at 3.4 V, Other inputs at V_{CC} or GND	5.5 V			1.35	PRO	1.5		1.5	mA
Ci	V _I = V _{CC} or GND	5 V		2.5	10				10	pF
Co	V _O = V _{CC} or GND	5 V		4.5						pF

* On products compliant to MIL-PRF-38535, this parameter is not production tested at $V_{CC} = 0 V$.

† This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

timing requirements over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

		T _A = 25°C		T _A = 25°C SN54AHC		SN54AHCT16373 SN74AHCT16373		T16373	UNIT
		MIN	MAX	MIN	_ МАХ	MIN	MAX	UNIT	
tw	Pulse duration, LE high	6.5		6.5	N.	6.5		ns	
t _{su}	Setup time, data before LE \downarrow	1.5		1.5		1.5		ns	
th	Hold time, data after LE \downarrow	3.5		3.5		3.5		ns	



SCLS336H - MARCH 1996 - REVISED JANUARY 2000

switching characteristics over recommended operating	free-air temperature range,
V_{CC} = 5 $\breve{V} \pm 0.5$ V (unless otherwise noted) (see Figure 7	1)

	FROM	то	LOAD	Τį	₄ = 25°C	;	SN54AHC	T16373	SN74AHC	T16373													
PARAMETER	(INPUT)	(OUTPUT)	CAPACITANCE	MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT												
^t PLH	D	Q	Ci = 15 pE		5.1*	8.5*	1*	9.5*	1	9.5	-												
^t PHL	U	Q	C _L = 15 pF		5.1*	8.5*	1*	9.5*	1	9.5	ns												
^t PLH	LE	Q	C _L = 15 pF		5*	8.5*	1*	9.5*	1	9.5	ns												
^t PHL	LC	Q	CL = 15 pr		5*	8.5*	1*	9.5*	1	9.5	115												
^t PZH	OE	Q	C _L = 15 pF		5*	9.5*	1*	10.5*	1	10.5	ns												
^t PZL	ÛE	Q	CL = 15 pr		5*	9.5*	1*	10.5*	1	10.5													
^t PHZ	OE	Q	C _I = 15 pF		6*	10.2*	1*	11*	1	11	ns												
^t PLZ	ÛE	Q	0 <u>[</u> = 15 pi		6.8*	10.2*	1*	۲ 11*	1	11	115												
^t PLH	D	Q	$C_{1} = 50 \text{pF}$		5.9	9.5	J	10.5	1	10.5	ns												
^t PHL	D		0L = 30 pi		5.9	9.5	7g	10.5	1	10.5	115												
^t PLH	LE	Q	CL = 50 pF		6.4	9.5	x 1	10.5	1	10.5	ns												
^t PHL			0L = 30 pi		5.9	9.5	1	10.5	1	10.5	115												
^t PZH	OE	Q	CL = 50 pF		6	10.5	1	11.5	1	11.5	ns												
^t PZL	ÛE	Q	CL = 30 pr		6	10.5	1	11.5	1	11.5	115												
^t PHZ	OE	Q	C _L = 50 pF		6.8	11.2	1	12	1	12	ns												
^t PLZ	UE	Q	Q			Q	Q Q	Q		L Q	Q	Q	Q	Q	oF = 20 bi.		7.8	11.2	1	12	1	12	115
^t sk(o) [†]			C _L = 50 pF			1**				1	ns												

* On products compliant to MIL-PRF-38535, this parameter is not production tested.

** On products compliant to MIL-PRF-38535, this parameter does not apply.

noise characteristics, V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C (see Note 4)

	PARAMETER			SN74AHCT16373			
	FARAMETER	MIN	TYP	MAX	UNIT		
VOL(P)	Quiet output, maximum dynamic V _{OL}		0.32	0.8	V		
VOL(V)	Quiet output, minimum dynamic V _{OL}		-0.1	-0.8	V		
VOH(V)	Quiet output, minimum dynamic V _{OH}		4.7		V		
V _{IH(D)}	High-level dynamic input voltage	2			V		
VIL(D)	Low-level dynamic input voltage			0.8	V		

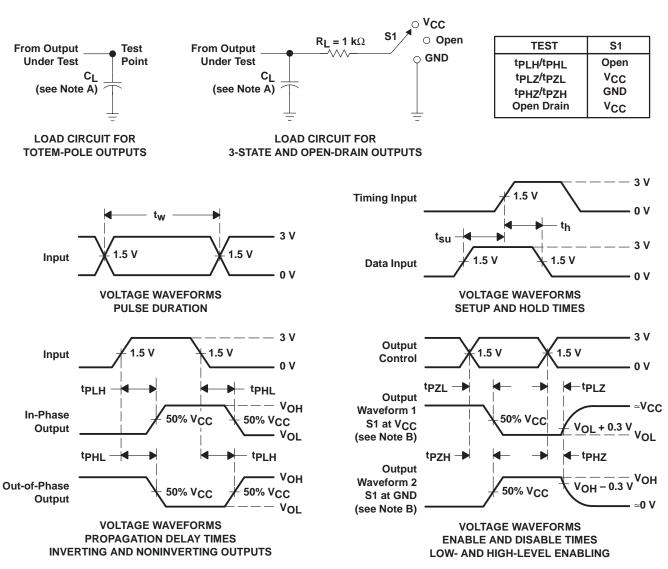
NOTE 4: Characteristics are for surface-mount packages only.

operating characteristics, V_{CC} = 5 V, T_A = 25°C

	PARAMETER		ONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	22	pF



SCLS336H – MARCH 1996 – REVISED JANUARY 2000



PARAMETER MEASUREMENT INFORMATION

NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, Z_O = 50 Ω , t_f \leq 3 ns, t_f \leq 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated